

## TO-92MOD Plastic-Encapsulate Transistors

### KSC2330 TRANSISTOR (NPN)

#### FEATURES

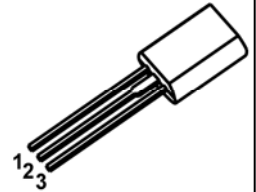
- General Purpose Amplifier Transistor

#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	300	V
$V_{CEO}$	Collector-Emitter Voltage	300	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current	100	mA
$P_C$	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^\circ\text{C/W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$

#### TO – 92MOD

1. EMITTER
2. COLLECTOR
3. BASE



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=5\text{mA}, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=200\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=10\text{V}, I_C=20\text{mA}$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		4		pF
Transition frequency	$f_T$	$V_{CE}=30\text{V}, I_C=10\text{mA}$		50		MHz

#### CLASSIFICATION OF $h_{FE}$

RANK	R	O	Y
RANGE	40-80	70-140	120-240